Peak gate current (t_p=20μs , T_j=125)	I_{GM}	4	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.7	kV

ELECTRICAL CHARACTERISTIC Tm ( )Tj EMC /P <</MCID 24 >>BDC 2.84 Tm W n E

ORDERING INFORMATION

J	CT	6	10	A
JieJie Microelectronics Co., Ltd.	SCRs	6:V_{DRM} /V_{RRM} 600V	$I_{T(RMS)}$:10A	A:TO-220A(Ins)

MARKING

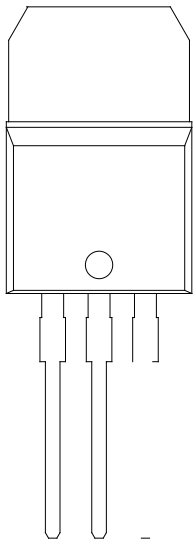


FIG.1: Maximum power dissipation versus RMS on-state current

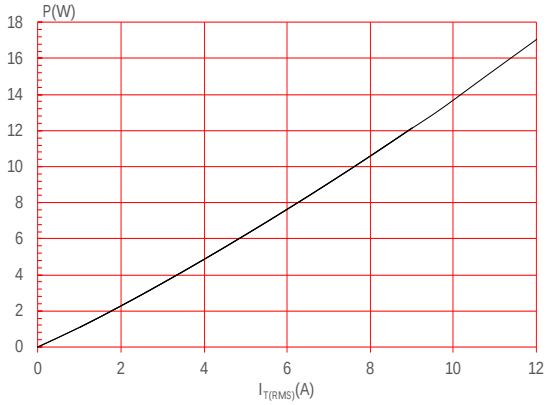


FIG.2: RMS on-state current versus case temperature

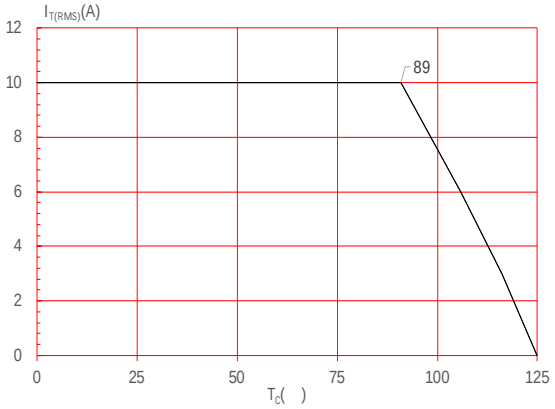


FIG.3: Surge peak on-state current versus number of cycles

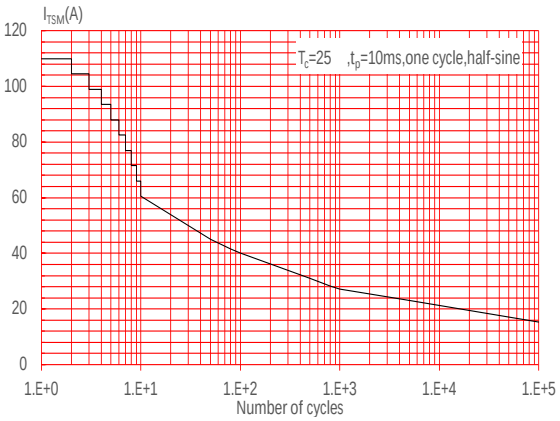


FIG.4: On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.



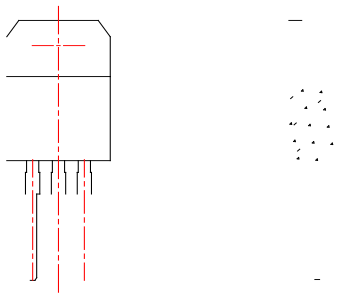
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT610A	600	10	TO-220A(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.12, 2023	A.1.0	Last update
Oct.10, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

PACKAGE MECHANICAL DATA



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